### **MOSFET** – Single, N-Channel, Gate ESD Protection, Small Signal, SC-75

### 20 V, 238 mA

#### Features

- Low Gate Charge for Fast Switching
- Small 1.6 x 1.6 mm Footprint
- ESD Protected Gate
- AEC-Q101 Qualified and PPAP Capable NVA4001N
- These Devices are Pb-Free and are RoHS Compliant

#### Applications

- Power Management Load Switch
- Level Shift
- Portable Applications such as Cell Phones, Media Players, Digital Cameras, PDA's, Video Games, Hand Held Computers, etc.

#### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise stated)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V <sub>DSS</sub>	20	V
Gate-to-Source Voltage		V <sub>GS</sub>	±10	V
Continuous Drain Current (Note 1)	Steady State = 25°C	۱ <sub>D</sub>	238	mA
Power Dissipation (Note 1)	Steady State = 25°C	PD	300	mW
Pulsed Drain Current	$t_P \le 10 \ \mu s$	I <sub>DM</sub>	714	mA
Operating Junction and Storage Temperature		T <sub>J</sub> , T <sub>STG</sub>	–55 to 150	°C
Continuous Source Current (Body Diode)		I <sub>SD</sub>	238	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		ΤL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	416	°C/W

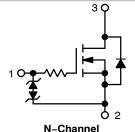
1. Surface-mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces).



#### **ON Semiconductor®**

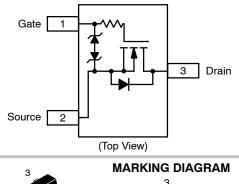
#### http://onsemi.com

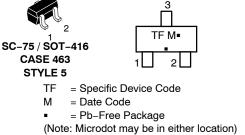
V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> Typ @ V <sub>GS</sub>	I <sub>D</sub> MAX (Note 1)
20 V	1.5 Ω @ 4.5 V	238 mA
	2.2 Ω @ 2.5 V	200 11# 1



PIN CONNECTIONS

SC-75 (3-Leads)





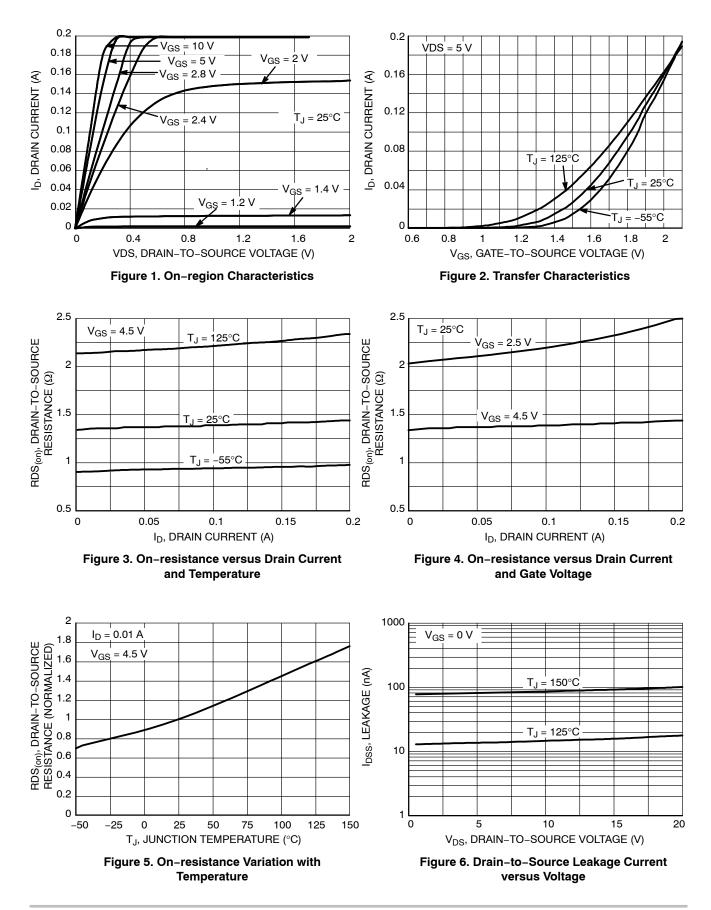
#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

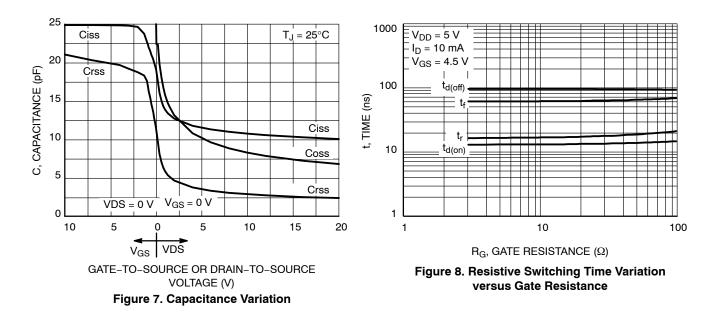
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
OFF CHARACTERISTICS						-
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS}$ = 0 V, $I_D$ = 100 $\mu$ A	20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 \text{ V}, \text{ V}_{DS} = 20 \text{ V}$			1.0	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±10 V			±100	μA
ON CHARACTERISTICS (Note 2)						-
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{DS}$ = 3 V, $I_D$ = 100 $\mu$ A	0.5	1.0	1.5	V
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	$V_{GS}$ = 4.5 V, $I_{D}$ = 10 mA		1.5	3.0	Ω
		$V_{GS}$ = 2.5 V, I <sub>D</sub> = 10 mA		2.2	3.5	
Forward Transconductance	9fs	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 10 mA		80		mS
CAPACITANCES				-		
Input Capacitance	C <sub>ISS</sub>			11.5	20	pF
Output Capacitance	C <sub>OSS</sub>	V <sub>DS</sub> = 5 V, f = 1 MHz, V <sub>GS</sub> = 0 V		10	15	
Reverse Transfer Capacitance	C <sub>RSS</sub>	103 01		3.5	6.0	
SWITCHING CHARACTERISTICS (Note 3)				-		
Turn-On Delay Time	t <sub>d(ON)</sub>			13		ns
Rise Time	t <sub>r</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 5 V,		15		
Turn-Off Delay Time	t <sub>d(OFF)</sub>	$I_D = 10 \text{ mA}, R_G = 10 \Omega$		98		ns
Fall Time	t <sub>f</sub>			60		
DRAIN-SOURCE DIODE CHARACTERISTICS	-		-	-	-	-
Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 10 mA		0.66	0.8	V

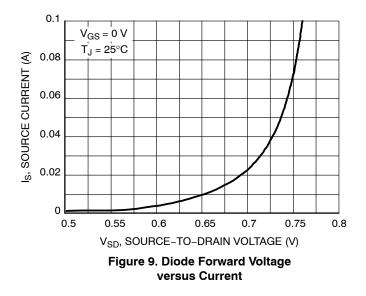
Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
Switching characteristics are independent of operating junction temperatures.

#### TYPICAL PERFORMANCE CURVES



#### **TYPICAL PERFORMANCE CURVES**



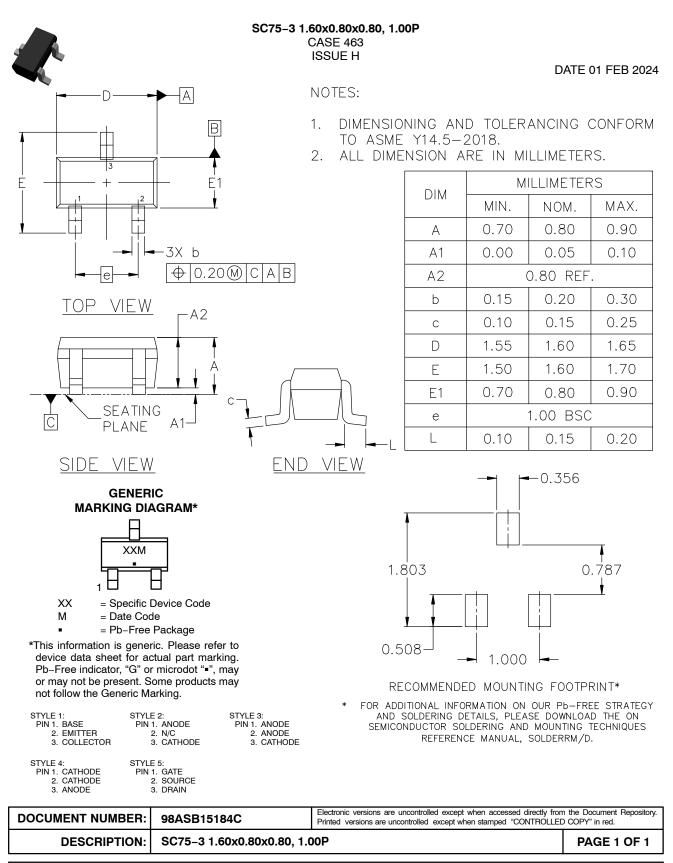


#### **ORDERING INFORMATION**

Order Number	Package	Shipping <sup>†</sup>
NTA4001NT1G	SC–75 (Pb–Free)	3000 / Tape & Reel
NVA4001NT1G	SC–75 (Pb–Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





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